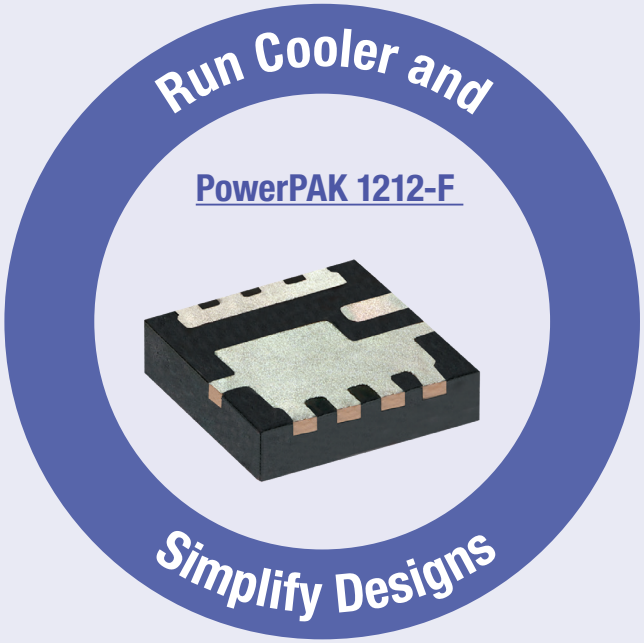
SiSD5300DN 30 V MOSFET in PowerPAK® 1212-F

Best in Class On-Resistance, Better Thermal Resistance, Easier Layout

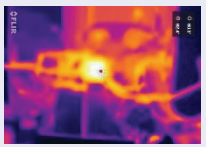
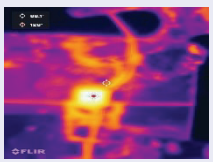
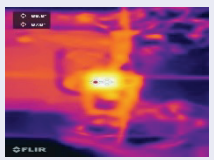
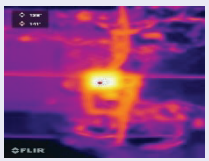
ADVANTAGES

- Flip technology with maximum source pad dimension of 4.13 mm^2 (vs. 0.36 mm^2 for PowerPAK 1212-8S) improves thermal dissipation
- Central gate design simplifies paralleling devices on a single-layer PCB
- Gen V silicon technology enables best in class
  - $R_{DS(on)}$ down to 0.71 mΩ
  - FOM = 42 mΩ*Q_g
- R_{thJA} = 18 °C/W
- 3.3 mm by 3.3 mm footprint



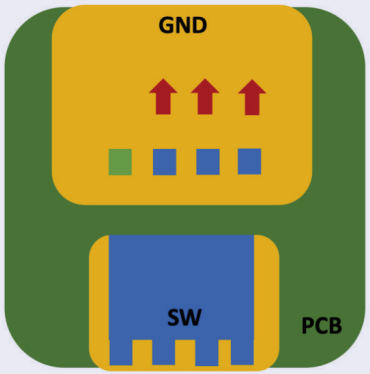
APPLICATIONS

WELDING EQUIPMENT
BATTERY MANAGEMENT SYSTEMS
POWER SUPPLIES / MODULES
SERVERS AND EDGE DEVICES
CLEANING ROBOTS
RADIO BASE STATIONS
SUPERCOMPUTERS
POWER TOOLS
LAWNMOWERS
TABLETS

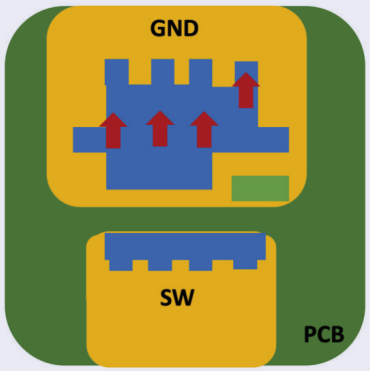
	PD = 1.0 W	Thermal Image	PD = 3.0 W	Thermal Image
PowerPAK 1212-F	62.4 °C		126 °C	
	-4.8 °C		-15 °C	
PowerPAK 1212-8S	67.6 °C		141 °C	

Compared to previous-generation MOSFETs in the same footprint, the SiSD5300DN in the PowerPAK 1212-F delivers lower temperature operation for the same level of current handling in a constant power comparison test.

PowerPAK 1212-8



PowerPAK 1212-F



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